

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

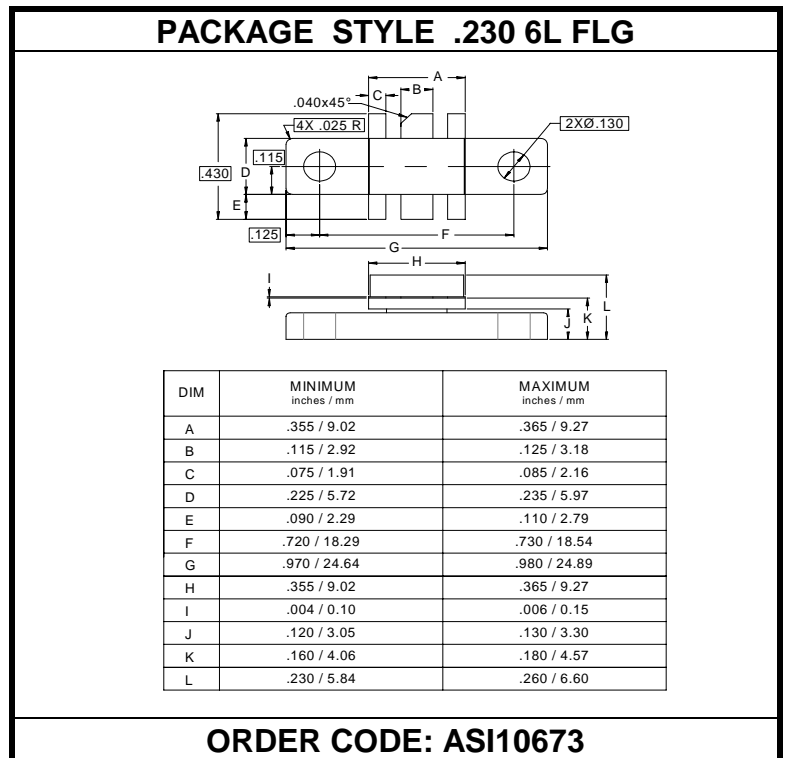
The **ASI UHBS60-2** is Designed for Class C, FM Base Station Applications up to 960 MHz.

**FEATURES:**

- Internal Input Matching Network
- $P_G = 7.0$  dB at 60 W/960 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	9.0 A
$V_{CBO}$	50 V
$V_{CEO}$	26 V
$V_{CES}$	50 V
$V_{EBO}$	4.0 V
$P_{DISS}$	190 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	0.9 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 50$ mA	50			V
$BV_{CES}$	$I_C = 50$ mA	50			V
$BV_{CEO}$	$I_C = 50$ mA	26			V
$BV_{EBO}$	$I_E = 10$ mA	3.0			V
$I_{CES}$	$V_{CE} = 20$ V			10	mA
$I_{CBO}$	$V_{CB} = 30$ V			5	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	20		100	---
$C_{ob}$	$V_{CB} = 24$ V $f = 1.0$ MHz			75	pF
$P_G$ $\eta_C$	$V_{CE} = 24$ V $P_{OUT} = 60$ W $f = 960$ GHz	7.0	50		dB %